



## DESCRIPTION

The AZ5325-01F is a low-capacitance Transient Voltage Suppressor (TVS) designed to provide electrostatic discharge (ESD) protection for data, control or power lines. With typical capacitance of 8pF only, The AZ5325-01F is designed to protect parasitic-sensitive systems against over-voltage and over-current transient events. It complies with IEC 61000-4-2 (ESD), Level 4 (±15kV air, ±8kV contact discharge), IEC 61000-4-4 (electrical fast transient - EFT) (40A, 5/50 ns), very fast charged device model (CDM) ESD and cable discharge event (CDE), etc.

The AZ5325-01F is uses ultra-small DFN1006 package. The AZ5325-01F is device can protect one data line. It offers system designers flexibility to protect single data line where space is a premium concern.

#### ORDERING INFORMATION

-Package: DFN1006

Material: RoHS compliant, Halogen free

- Packing: Tape & Reel

Quantity per reel: 10,000pcs

## **FEATURES**

 Transient protection for high-speed data lines IEC 61000-4-2 (ESD) ±15kV (Air) ±8kV (Contact)

IEC 61000-4-4 (EFT) 40A (5/50 ns) Cable Discharge Event (CDE)

- Package optimized for high-speed lines Ultra-small package (1.0mm·0.6mm·0.4mm) — Protects one data, control or power line —Low capacitance
- Low leakage current
- Low clamping

#### voltage

 Each I/O pin can withstand over 1000 ESD strikes for ±8kV contact discharge

## MACHANICAL DATA

-DFN1006 package -

Flammability Rating: UL 94V-0

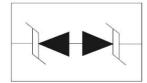
- Packaging: Tape and Reel
- High temperature soldering

guaranted:260°C/10s — Reel size: 7 inch

#### **APPLICATIONS**

- Portable Electronics
- Desktops, Servers and Notebooks
- -Cellular Phones
- -MP3 Ports
- Digital Ports
- Subscriber Identity Module (SIM) card

## CIRCUIT DIAGRAM



## PIN CONFIGURATION





ABSOLUTE MAXIMUM RATING							
Symbol	Parameter	Value	Units				
P <sub>PP</sub>	Peak Pulse Power (8/20µs)	100	W				
Tj	Operating Temperature	-55/+125	°C				
Тѕтс	Storage Temperature	-55/+150	°C				

ELECTRICAL CHARACTERISTICS (Tamb=25°C)							
Symbol	Parameter	Test Condition	Min	Тур	Max	Units	
<b>V</b> RWM	Reverse Stand-Off Voltage				5.0	٧	
<b>V</b> BR	Reverse Breakdown voltage	I <sub>T</sub> =1mA	6.0			V	
IR	Reverse leakage current.	V <sub>RWM</sub> =5V			1	μΑ	
Ірр	Peak Pulse Current	tp=8/20us			5	Α	
<b>V</b> C	Clamping Voltage	Ipp=1A, tp=8/20us			9.5	V	
		IPP=5A, tP=8/20us		13	15		
CJ	Junction Capacitance	V <sub>R</sub> =0V,f=1MHz		8	15	pF	



## **ELECTRICAL CHARACTERISTICS CURVE**

Figure 1: Peak Pulse Power Vs Pulse Time

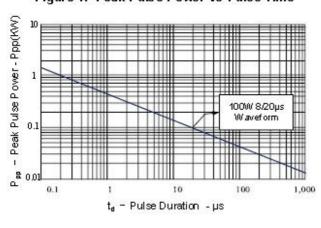


Figure 2: Power Derating Curve 110 = 100 Percent of Rated Power for 90 80 70 60 50 40 30 20 10 0 150

Figure 3: Clamping Voltage vs. Peak Pulse Current

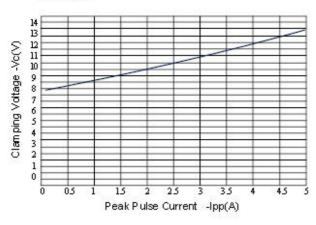


Figure 4: Normalized Junction Capacitance vs. Reverse Voltage

Ambient Temperature - TA (°C)

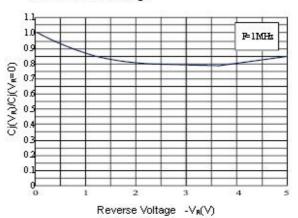


Figure 5: Pulse Waveform

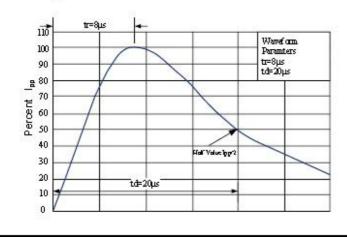
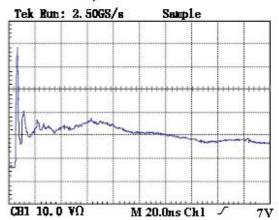
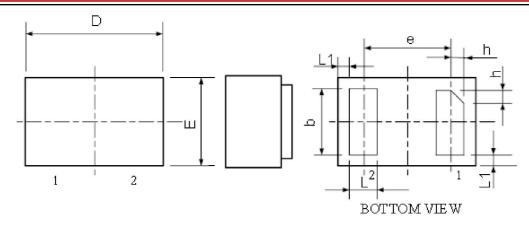


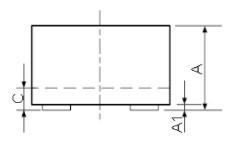
Figure 6: ESD Clamping (8kV Contact per IEC 61000-4-2)





# **DFN1006 PACKAGE OUTLINE DIMENSIONS**





Complete al	Dimensions In Millimeters			
Symbol	Minimum	Maximum		
А	0.450	0.550		
A1	0.000	0.050		
b	0.45	0.55		
С	0.12	0.18		
D	0.950	1.050		
e	0.65BSC			
E	0.550	0.650		
L	0.200	0.300		
L1	0.05REF			
h	0.07	0.17		